

Abstract

A method for producing a semiconductor integrated circuit device, and a semiconductor integrated circuit device are disclosed. In the method, during a photomask process of forming a logic gate electrode (G5, G6) in a peripheral circuit region (ER2), a surrounding conductive layer (Ga, Gb) in a memory circuit region (ER1) is divided into a first select gate electrode (G2a, G2b) and a second select gate electrode (G3a, G3b) electrically separated from each other. Thus, even when the first select gate electrode (G2a, G2b) and the second select gate electrode (G3a, G3b) are formed to be separately controllable, it is not necessary to perform an extra dedicated photomask process of fabricating only the memory circuit region (ER1), in addition to a conventional dedicated photomask process of fabricating only the memory circuit region, thereby production cost is reduced.